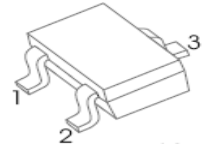
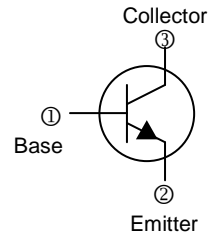




MMBT5551W NPN Silicon Plastic-Encapsulate Transistor

FEATURE

- Ideal for Medium Power Amplification and Switching
- Also Available in Lead Free Version
- Complementary to MMBT5401W



MARKING: K4N

SOT-323

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current-Continuous	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating & Storage Temperature	T_j, T_{STG}	150, -55 ~ 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180		V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160		V	$I_C=1\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6		V	$I_E=10\mu\text{A}, I_C=0$
Collector Cutoff Current	I_{CBO}		50	nA	$V_{CB}=120\text{V}, I_E=0$
Emitter Cutoff Current	I_{EBO}		50	nA	$V_{EB}=4\text{V}, I_C=0$
DC Current Gain	h_{FE1}	80			$V_{CE}=5\text{V}, I_C=1\text{mA}$
	h_{FE2}	80	250		$V_{CE}=5\text{V}, I_C=10\text{mA}$
	h_{FE3}	30			$V_{CE}=5\text{V}, I_C=50\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.15	V	$I_C=10\text{mA}, I_B=1\text{mA}$
	$V_{CE(sat)}$		0.2	V	$I_C=50\text{mA}, I_B=5\text{mA}$
Base-Emitter Voltage	$V_{BE(sat)}$		1	V	$I_C=10\text{mA}, I_B=1\text{mA}$
	$V_{BE(sat)}$		1	V	$I_C=50\text{mA}, I_B=5\text{mA}$
Transition Frequency	f_T	100	300	MHz	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$
Collector Output Capacitance	C_{ob}		6	pF	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$
Noise Figure	NF		8	dB	$V_{CE}=5\text{V}, I_C=0.2\text{mA}, f=1\text{KHz}, R_S=1\text{K}\Omega$



CHARACTERISTIC CURVES

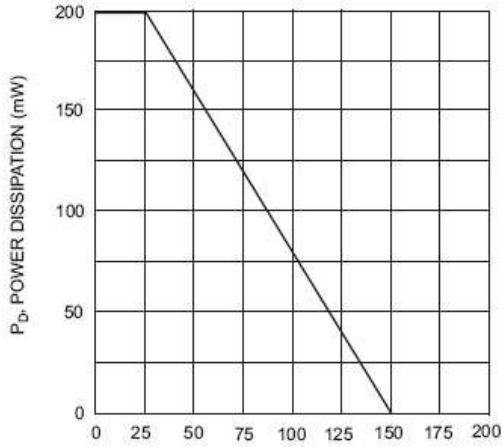


Fig. 1, Max Power Dissipation vs Ambient Temperature

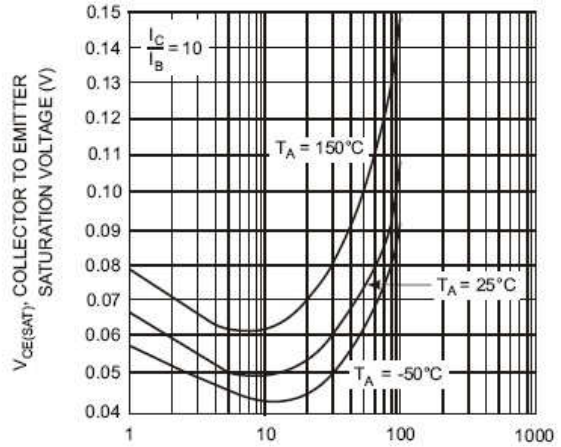


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

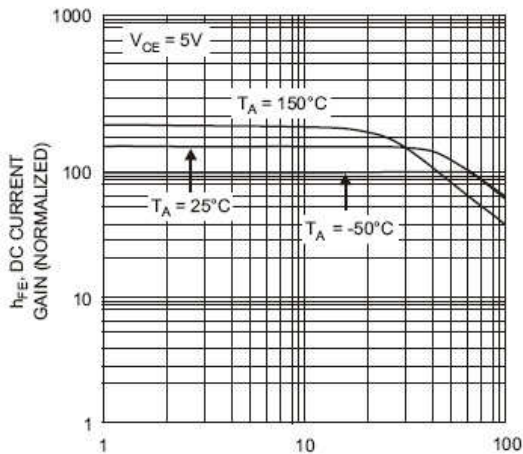


Fig. 3, DC Current Gain vs Collector Current

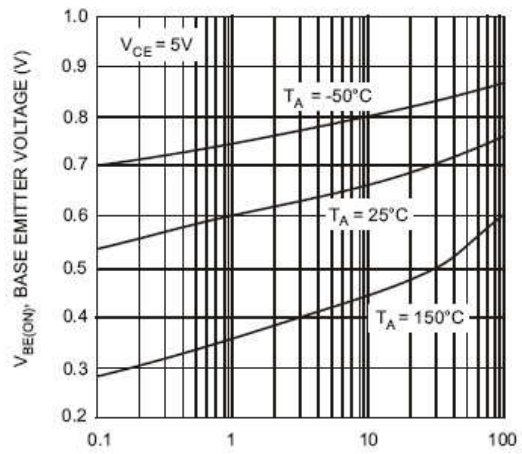


Fig. 4, Base Emitter Voltage vs. Collector Current

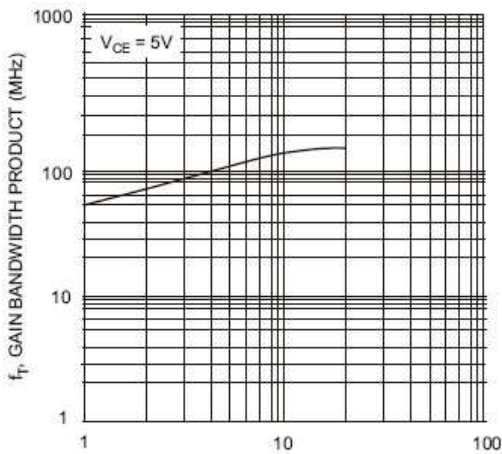
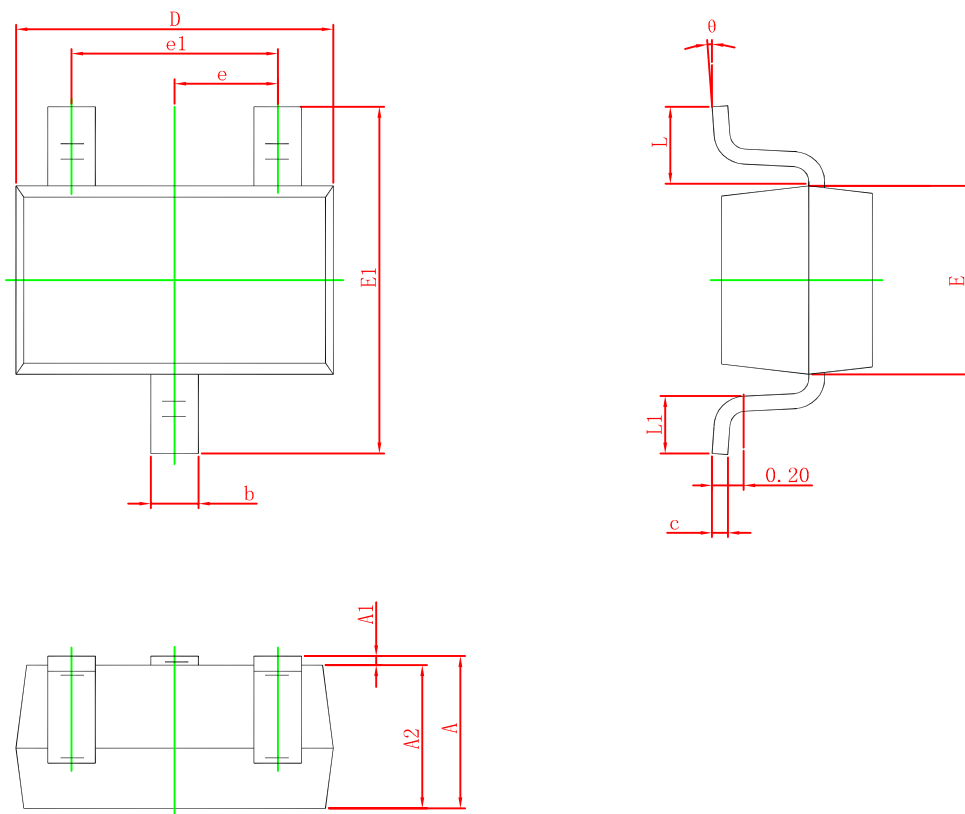


Fig. 5, Gain Bandwidth Product vs. Collector Current



SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°